Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

DMMT5551/DMMT5551S

MATCHED NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

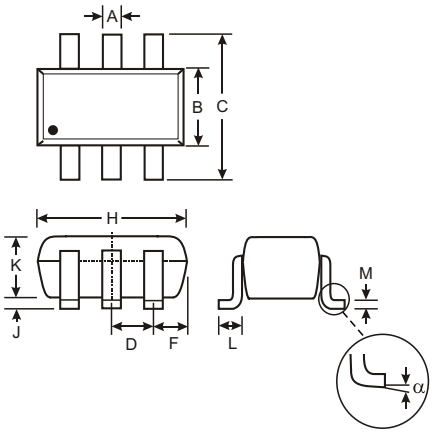
NEW PRODUCT

Features

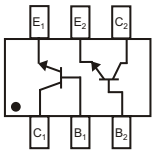
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DMMT5401)
- Ideal for Medium Power Amplification and Switching
- Intrinsically Matched NPN Pair (Note 1)
- 2% Matched Tolerance, h_{FE}, $V_{CE(SAT)}$, $V_{BE(SAT)}$
- 1% Matched Tolerance, Available (Note 2)
- Also Available in Lead Free Version

Mechanical Data

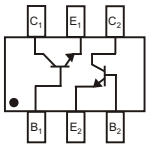
- Case: SOT-26, Molded Plastic
- Case Material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish). Please see Ordering Information, Note 8, on Page 2
- Terminal Connections: See Diagram
- Marking (See Page 2): K4R & K4T
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approx.)



SOT-26			
Dim	**Min**	**Max**	**Typ**
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
F	—	—	0.55
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			



DMMT5551
(K4R Marking Code)



DMMT5551S
(K4T Marking Code)

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 3)	I_C	200	mA
Power Dissipation (Note 3, 4)	P_d	300	mW
Thermal Resistance, Junction to Ambient (Note 3)	$R_{\theta JA}$	417	K/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	°C

Notes:
1. Built with adjacent die from a single wafer.
2. Contact the Diodes, Inc. Sales department.
3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
4. Maximum combined dissipation.

NEW PRODUCT

Electrical Characteristics @ T_A = 25°C unless otherwise specified

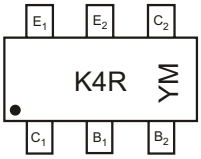
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	180	—	V	I_C = 100μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	160	—	V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	I_E = 10μA, I_C = 0
Collector Cutoff Current	I_{CBO}	—	50	nA μA	V_{CB} = 120V, I_E = 0 V_{CB} = 120V, I_E = 0, T_A = 100°C
Emitter Cutoff Current	I_{EBO}	—	50	nA	V_{EB} = 4.0V, I_C = 0
ON CHARACTERISTICS (Note 5)					
DC Current Gain (Note 6)	h_{FE}	80 80 30	— 250 —	—	I_C = 1.0mA, V_{CE} = 5.0V I_C = 10mA, V_{CE} = 5.0V I_C = 50mA, V_{CE} = 5.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.15 0.20	V	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	1.0	V	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	6.0	pF	V_{CB} = 10V, f = 1.0MHz, I_E = 0
Small Signal Current Gain	h_{FE}	50	250	—	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f_T	100	300	MHz	V_{CE} = 10V, I_C = 10mA, f = 100MHz
Noise Figure	NF	—	8.0	dB	V_{CE} = 5.0V, I_C = 200μA, R_S = 1.0kΩ, f = 1.0kHz

Ordering Information (Note 7)

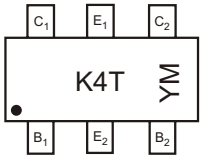
Device	Packaging	Shipping
DMMT5551-7	SOT-26	3000/Tape & Reel
DMMT5551S-7	SOT-26	3000/Tape & Reel

Notes:
5. Short duration test pulse used to minimize self-heating effect.
6. The DC Current Gain, h_{FE}, (matched at I_C = 10mA and V_{CE} = 5V) Collector Emitter Saturation Voltage, $V_{CE(SAT)}$, and Base Emitter Saturation Voltage, $V_{BE(SAT)}$ are matched with typical matched tolerances of 1% and maximum of 2%.
7. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.
8. For Lead Free version (with Lead Free terminal finish) part number, please add "-F" suffix to part number above. Example: DMMT5551-7-F.

Marking Information



K4R = DMMT5551 Product Type Marking Code
YM = Date Code Marking
Y = Year ex: P = 2003
M = Month ex: 9 = September



K4T = DMMT5551S Product Type Marking Code
YM = Date Code Marking
Y = Year ex: P = 2003
M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009
Code	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

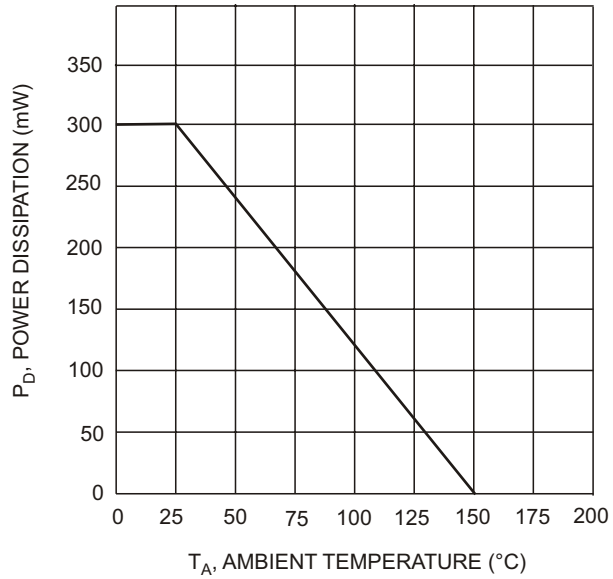


Fig. 1, Max Power Dissipation vs Ambient Temperature

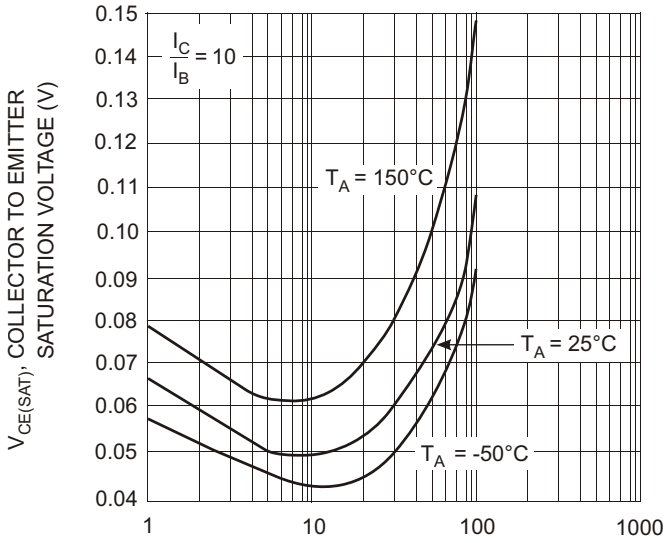


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

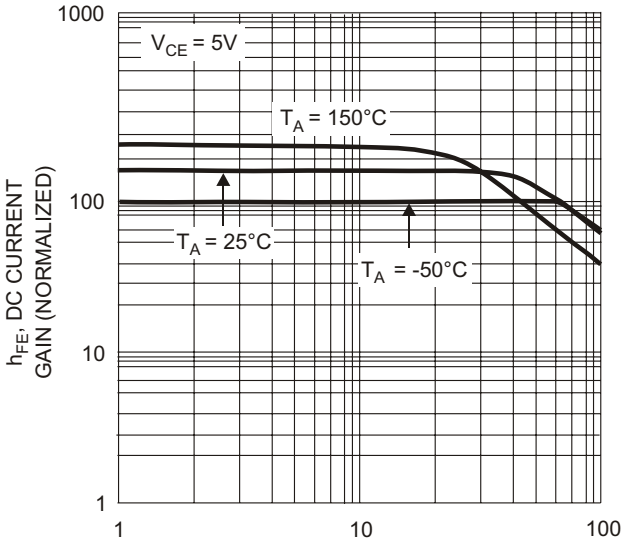


Fig. 3, DC Current Gain vs Collector Current

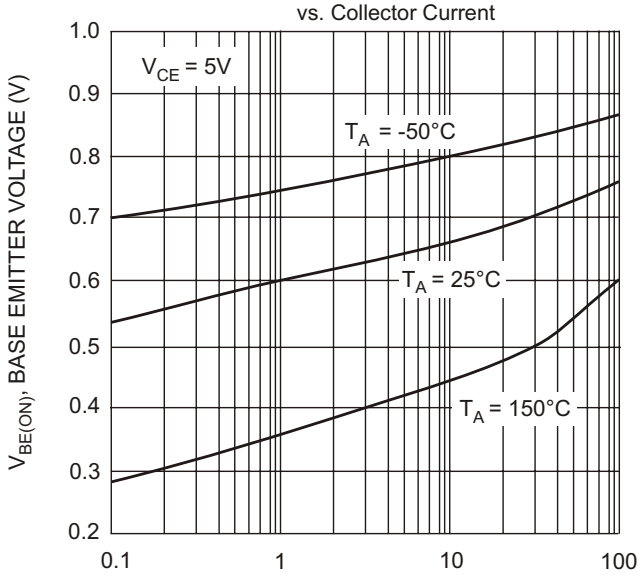


Fig. 4, Base Emitter Voltage vs. Collector Current

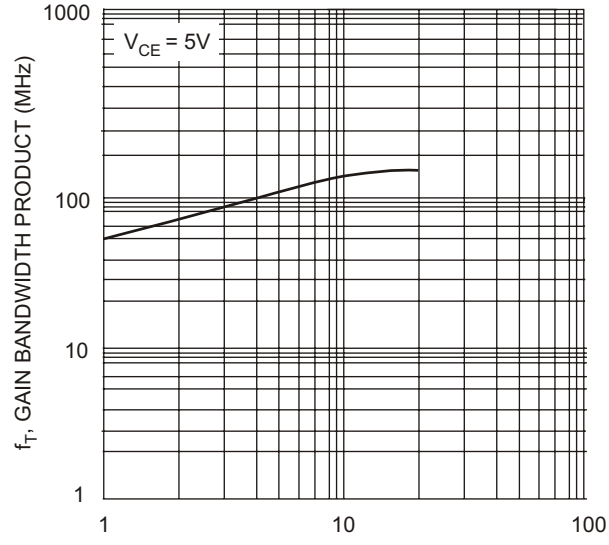


Fig. 5, Gain Bandwidth Product vs. Collector Current